

SCT2160KE

N-channel SiC power MOSFET

V _{DSS}	1200V
R _{DS(on)} (Typ.)	160mΩ
I _D	22A
P_D	165W

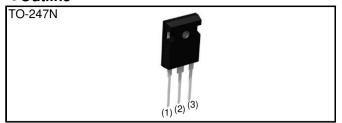
Features

- 1) Low on-resistance
- 2) Fast switching speed
- 3) Fast reverse recovery
- 4) Easy to parallel
- 5) Simple to drive
- 6) Pb-free lead plating; RoHS compliant

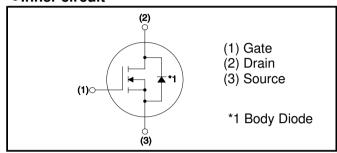
Application

- Solar inverters
- DC/DC converters
- · Induction heating
- Motor drives

Outline



•Inner circuit



Packaging specifications

Packa	age	TO-247N
	Packing	Tube
	Reel size (mm) Tape width (mm)	-
Type		-
Туре	Basic ordering unit (pcs)	30
	Packing code	C11
	Marking	SCT2160KE

● Absolute maximum ratings (Ta = 25°C)

Parameter		Symbol	Value	Unit
Drain - Source voltage		$V_{ extsf{DSS}}$	1200	V
Continuous drain current	$T_c = 25^{\circ}C$	I _D *1	22	А
Continuous drain current	T _c = 100°C	I _D *1	16	Α
Pulsed drain current		I _{D,pulse} *2	55	Α
Gate - Source voltage (DC)		V_{GSS}	-6 to 22	V
Gate - Source surge voltage (T _{surge} < 300nsec)		V _{GSS-surge} *3	-10 to 26	V
Power dissipation (T _c = 25°C)		P_{D}	165	W
Junction temperature		T _j	175	°C
Range of storage temperature		T _{stg}	-55 to +175	°C

●Electrical characteristics (T_a = 25°C)

Parameter	Symbol	Conditions	Values			Unit
i arameter	Symbol	Conditions	Min.	Тур.	Max.	Offic
Drain - Source breakdown voltage	$V_{(BR)DSS}$	$V_{GS} = 0V$, $I_D = 1mA$	1200	ı	ı	V
Zero gate voltage drain current	I _{DSS}	V_{DS} = 1200V, V_{GS} = 0V T_j = 25°C T_j = 150°C	1 1	1 2	10	μΑ
Gate - Source leakage current	I _{GSS+}	$V_{GS} = +22V, V_{DS} = 0V$	ı	ı	100	nA
Gate - Source leakage current	I _{GSS-}	$V_{GS} = -6V, V_{DS} = 0V$	-	-	-100	nA
Gate threshold voltage	V _{GS (th)}	$V_{DS} = V_{GS}$, $I_D = 2.5 \text{mA}$	1.6	2.8	4.0	V

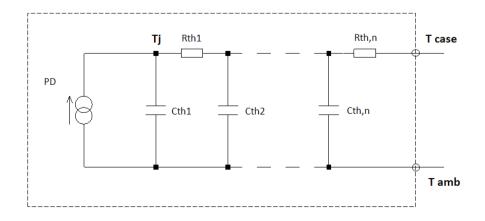
●Thermal resistance

Parameter	Symbol	Values			Unit
Farameter	Symbol	Min.	Тур.	Max.	Offic
Thermal resistance, junction - case	R_{thJC}	1	0.70	0.91	°C/W
Thermal resistance, junction - ambient	R_{thJA}	-	-	50	°C/W
Soldering temperature, wavesoldering for 10s	T _{sold}	-	-	265	°C

●Typical Transient Thermal Characteristics

Symbol	Value	Unit
R _{th1}	9.61E-02	
R _{th2}	4.04E-01	K/W
R _{th3}	1.96E-01	

Symbol	Value	Unit
C_{th1}	1.55E-03	
C _{th2}	5.23E-03	Ws/K
C _{th3}	8.33E-02	



●Electrical characteristics (T_a = 25°C)

Darameter	Cumbal	Conditions	Values			Unit
Parameter	Symbol		Min.	Тур.	Max.	Offic
		$V_{GS} = 18V, I_D = 7A$				
Static drain - source on - state resistance	R _{DS(on)} *4	$T_j = 25$ °C	-	160	208	mΩ
		T _j = 125°C	-	226	-	
Gate input resistance	R_{G}	f = 1MHz, open drain	-	13.7	-	Ω
Transconductance	g _{fs} *4	$V_{DS} = 10V, I_{D} = 7A$	-	2.4	-	S
Input capacitance	C _{iss}	$V_{GS} = 0V$	-	1200	1	
Output capacitance	C _{oss}	$V_{DS} = 800V$	-	45	-	рF
Reverse transfer capacitance	C _{rss}	f = 1MHz	-	7	-	
Effective output capacitance, energy related	C _{o(er)}	$V_{GS} = 0V$ $V_{DS} = 0V$ to 500V	-	71	-	pF
Turn - on delay time	t _{d(on)} *4	$V_{DD} = 400V, I_{D} = 7A$	-	23	-	
Rise time	t _r *4	$V_{GS} = 18V/0V$	-	25	-	
Turn - off delay time	t _{d(off)} *4	$R_L = 57\Omega$	-	67	-	ns
Fall time	t _f *4	$R_G = 0\Omega$	-	27	-	
Turn - on switching loss	E _{on} *4	$V_{DD} = 600V, I_{D} = 7A$ $V_{GS} = 18V/0V$	-	126	-	1
Turn - off switching loss	E _{off} *4	R _G = 0Ω, L=500μH *E _{on} includes diode reverse recovery	-	55	-	μJ

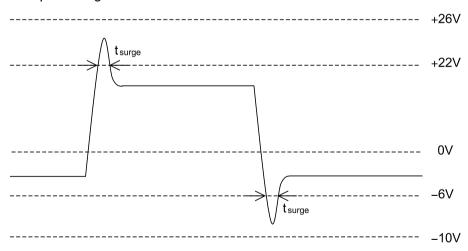
●Gate Charge characteristics (T_a = 25°C)

Parameter	Symbol	Conditions	Values			Lloit
			Min.	Тур.	Max.	Unit
Total gate charge	Q_g^{*4}	$V_{DD} = 400V$	-	62	-	
Gate - Source charge	Q _{gs} *4	$I_D = 7A$	-	14	-	nC
Gate - Drain charge	Q _{gd} *4	$V_{GS} = 18V$	-	20	-	
Gate plateau voltage	V _(plateau)	$V_{DD} = 400V, I_D = 7A$	-	9.6	-	V

●Body diode electrical characteristics (Source-Drain) (T_a = 25°C)

Parameter	Symbol	Conditions	Values			Unit
- Farameter	Symbol	Conditions	Min.	Тур.	Max.	UTIIL
Inverse diode continuous, forward current	l _S *1	-T _c = 25°C	-	-	22	А
Inverse diode direct current, pulsed	I _{SM} *2		-	-	55	Α
Forward voltage	V _{SD} *4	$V_{GS} = 0V, I_{S} = 7A$	-	4.1	-	V
Reverse recovery time	t _{rr} *4		-	26	-	ns
Reverse recovery charge	Q _{rr} *4	I _F = 7A, V _R = 400V di/dt = 160A/μs	-	39	-	nC
Peak reverse recovery current	l _{rrm} *4		-	3.0	-	Α

^{*3} Example of acceptable Vgs waveform



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*4 Pulsed

^{*1} Limited only by maximum temperature allowed.

^{*2} PW \leq 10 μ s, Duty cycle \leq 1%

Fig.1 Power Dissipation Derating Curve

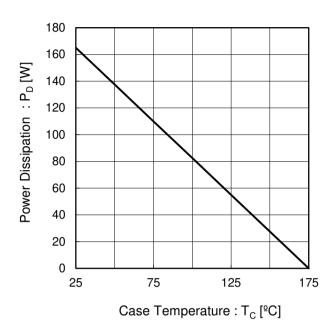
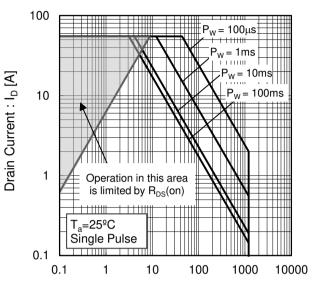


Fig.2 Maximum Safe Operating Area



Drain - Source Voltage : V_{DS} [V]

Fig.3 Typical Transient Thermal Resistance vs. Pulse Width

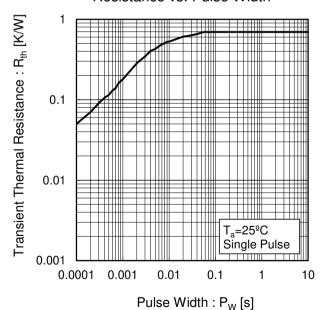


Fig.4 Typical Output Characteristics(I)

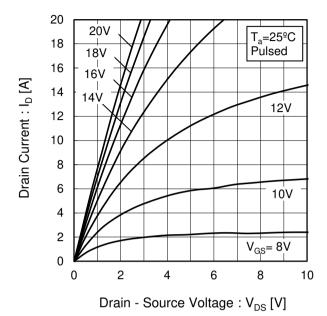
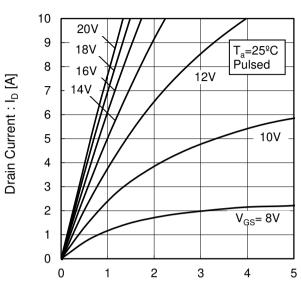


Fig.5 Typical Output Characteristics(II)



Drain - Source Voltage : V_{DS} [V]

Fig.6 $T_j = 150^{\circ}C$ Typical Output Characteristics(I)

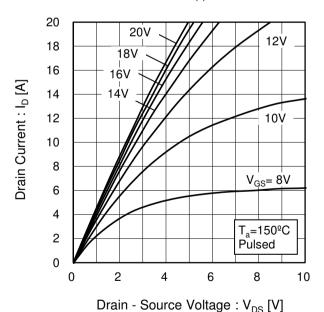
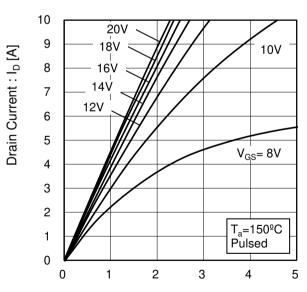


Fig.7 $T_j = 150^{\circ}C$ Typical Output Characteristics(II)



Drain - Source Voltage: V_{DS} [V]

Fig.8 Typical Transfer Characteristics (I)

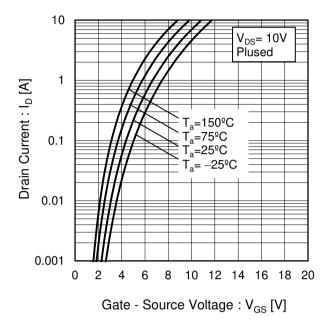


Fig.9 Typical Transfer Characteristics (II)

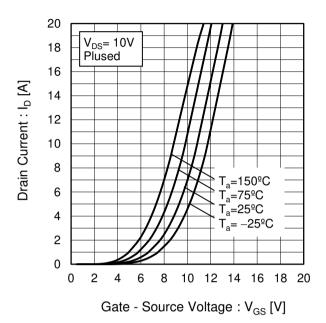


Fig.10 Gate Threshold Voltage vs. Junction Temperature

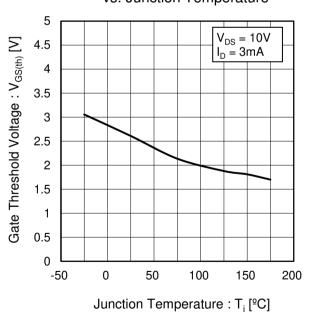


Fig.11 Transconductance vs. Drain Current

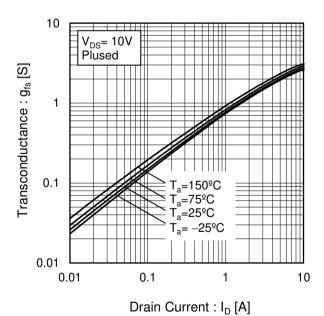


Fig.12 Static Drain - Source On - State
Resistance vs. Gate Source Voltage

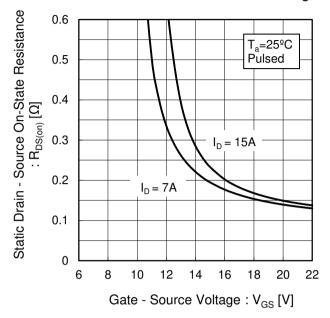


Fig.13 Static Drain - Source On - State
Resistance vs. Junction Temperature

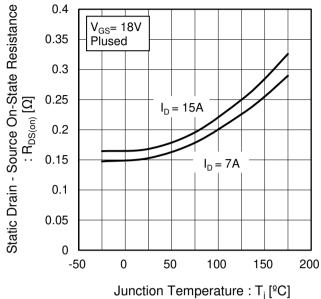


Fig.14 Static Drain - Source On - State Resistance vs. Drain Current

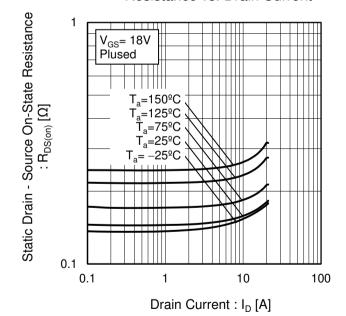


Fig.15 Typical Capacitance vs. Drain - Source Voltage

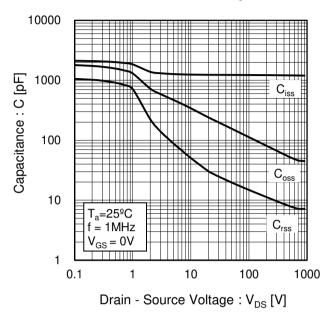


Fig.16 C_{OSS} Stored Energy

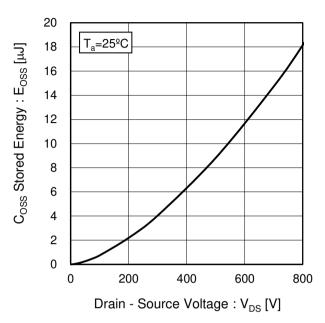


Fig.17 Switching Characteristics

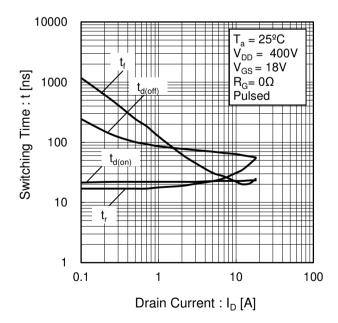


Fig.18 Dynamic Input Characteristics

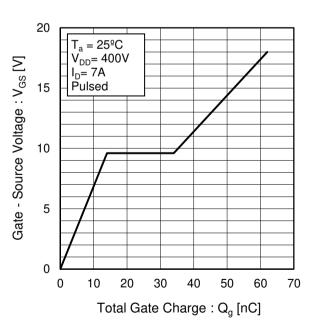


Fig.19 Typical Switching Loss vs. Drain - Source Voltage

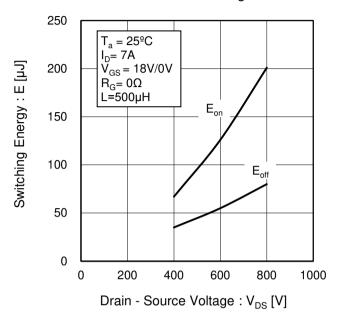


Fig.20 Typical Switching Loss vs. Drain Current

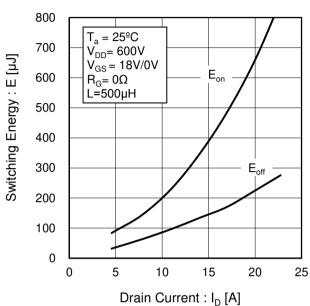


Fig.21 Typical Switching Loss vs. External Gate Resistance

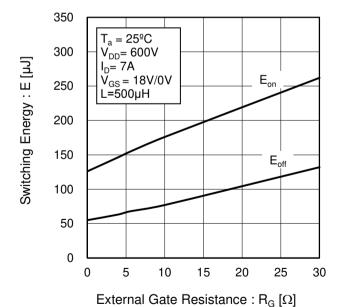


Fig.22 Inverse Diode Forward Current vs. Source - Drain Voltage

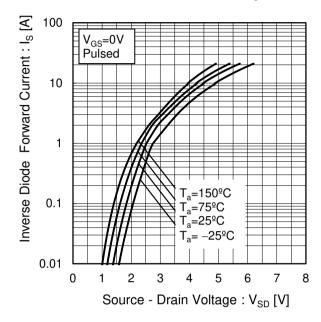
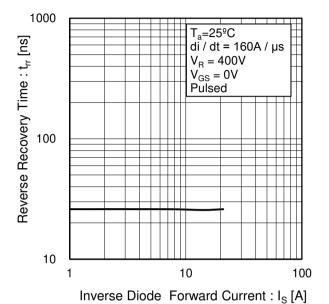


Fig.23 Reverse Recovery Time vs.Inverse Diode Forward Current



Measurement circuits

Fig.1-1 Switching Time Measurement Circuit

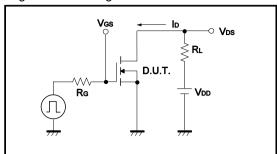


Fig.2-1 Gate Charge Measurement Circuit

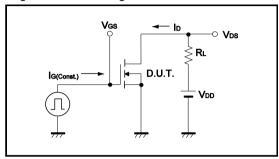


Fig.3-1 Switching Energy Measurement Circuit

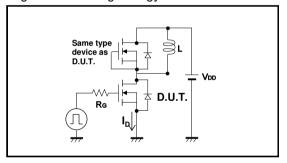


Fig.4-1 Reverse Recovery Time Measurement Circuit Fig.4-2 Reverse Recovery Waveform

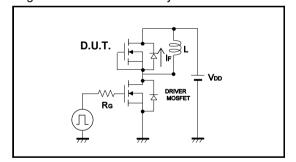


Fig.1-2 Switching Waveforms

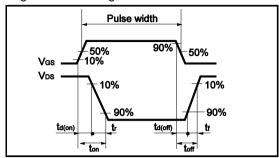


Fig.2-2 Gate Charge Waveform

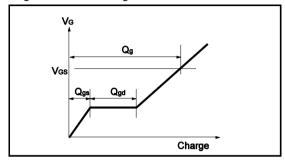
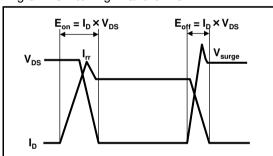
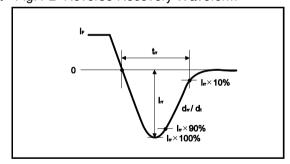


Fig.3-2 Switching Waveforms





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